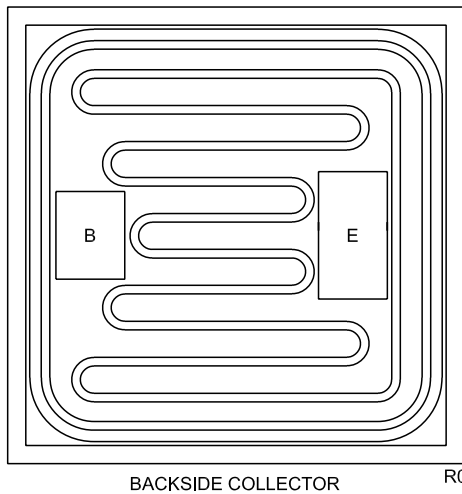


PROCESS DETAILS

Process	Epitaxial Planar
Die Size	31.5 x 31.5 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	4.7 x 6.7 MILS
Emitter Bonding Pad Area	4.7 x 8.7 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

11,210

PRINCIPAL DEVICE TYPES

CMPT404A
MPS404A

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R0 (5- January 2006)